

AMENDMENTS TO THE CLAIMS:

Please amend claims 1, 9, 14, 19, 24, 25, 28 and 35 as indicated below. This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A stencil mask comprising:
a conductive thin film ~~with~~ having openings in the film;
an insulating film formed in ~~[[the]]~~ a region of the conductive thin film excluding the openings;
a conductive support formed on the insulating film; and
a conducting member which is formed through the insulating film in a part of the region
and which connects the conductive support and the conductive thin film electrically.
2. (Original) The stencil mask according to claim 1, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.
3. (Original) The stencil mask according to claim 1, wherein the conductive thin film and the conductive support are made of silicon.
4. (Original) The stencil mask according to claim 1, wherein the conducting member is made of tungsten.

5. (Original) The stencil mask according to claim 1, further comprising silicon or silicide formed on the surface of the conducting member.

6. (Original) The stencil mask according to claim 1, wherein the conducting member is formed in the conductive support.

7. (Original) The stencil mask according to claim 1, wherein the conducting member is formed in the conductive thin film.

8. (Original) The stencil mask according to claim 1, wherein the conducting member is formed on and in the conductive thin film.

9. (Currently Amended) A stencil mask comprising:

a conductive thin film ~~which has~~ having a first region and a second region, the second region being outside the first region, and the first region including a plurality of first openings;

an insulating film which is formed ~~in a region corresponding to~~ on the second region
[[of]] on a first side of the conductive thin film;

a conductive support which is formed ~~in a region corresponding to the second region of the conductive thin film via~~ on the insulating film;

a second opening which is formed through the conductive support and the insulating film in a part of the second region; and

a conducting member which is provided in the second opening and which connects the conductive thin film and the conductive support electrically.

10. (Original) The stencil mask according to claim 9, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

11. (Original) The stencil mask according to claim 9, wherein the conductive thin film and the conductive support are made of silicon.

12. (Original) The stencil mask according to claim 9, wherein the conducting member is made of tungsten.

13. (Original) The stencil mask according to claim 9, further comprising silicon or silicide formed on the surface of the conducting member.

14. (Currently Amended) A stencil mask comprising:
a conductive thin film ~~which has~~ having a first region and a second region, the first region including a plurality of first openings;
an insulating film formed ~~corresponding to~~ on the second region of the conductive thin film;
a conductive support formed on the insulating film;

a second opening ~~made~~ formed in the conductive thin film and the insulating film in a part of the second region ~~of the conductive thin film~~; and

a conducting member which is formed in the second opening and which connects the conductive thin film and the conductive support electrically.

15. (Original) The stencil mask according to claim 14, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

16. (Original) The stencil mask according to claim 14, wherein the conductive thin film and the conductive support are made of silicon.

17. (Original) The stencil mask according to claim 14, wherein the conducting member is made of tungsten.

18. (Original) The stencil mask according to claim 14, further comprising silicon or silicide formed on the surface of the conducting member.

19. (Currently Amended) A stencil mask comprising:
a conductive thin film ~~which has~~ having a first region and a second region, the first region including a plurality of first openings;
an insulating film formed ~~corresponding to~~ on the second region ~~of the conductive thin film~~;
film;

a conductive support formed on the insulating film;

a second opening ~~made~~ formed in the conductive thin film and the insulating film in a part of the second region of the conductive thin film; and

a conducting member which is formed on the surface of the conductive thin film and in the second opening and which connects the conductive thin film and the conductive support electrically.

20. (Original) The stencil mask according to claim 19, wherein the electrical conductivity of the conducting member is higher than that of each of the conductive thin film and the conductive support.

21. (Original) The stencil mask according to claim 19, wherein the conductive thin film and the conductive support are made of silicon.

22. (Original) The stencil mask according to claim 19, wherein the conducting member is made of tungsten.

23. (Original) The stencil mask according to claim 19, further comprising silicon or silicide formed on the surface of the conducting member.

24. (Currently Amended) A mask forming substrate comprising:
a conductive thin film having a first region and a second region, the second region being outside the first region;

an insulating film formed on the conductive thin film;
a conductive support formed on the insulating film;
an opening ~~made~~ formed in the conductive support and a third region of the insulating film corresponding to a part of the second region ~~of the conductive thin film~~; and
a conducting member which is formed in the opening and which connects the conductive thin film and the conductive support electrically.

25. (Currently Amended) The mask forming substrate according to claim 24, wherein the electrical conductivity of the conducting member is ~~equal to or~~ higher than that of each of the conductive thin film and the conductive support.

26. (Original) The mask forming substrate according to claim 24, wherein the conductive thin film and the conductive support are made of silicon.

27. (Original) The stencil mask according to claim 24, wherein the conducting member is made of tungsten.

28. (Currently Amended) A mask forming substrate comprising:
a conductive thin film having a first region and a second region, the second region being outside the first region;

an insulating film formed on the conductive thin film;
a conductive support formed on the insulating film;

an opening ~~made~~ formed in the conductive thin film and ~~a region of~~ the insulating film corresponding to a part of the second region ~~of the conductive thin film~~; and

a conducting member which is formed on the conductive thin film and in the opening and which connects the conductive thin film and the conductive support electrically.

29. (Withdrawn) A stencil mask manufacturing method comprising:

making a plurality of openings in a first region of a conductive thin film of an SOI substrate which includes a substrate, an insulating film formed on the substrate, and the conductive thin film with the first region and a second region formed on the insulating film;

forming a support by removing the substrate in a region corresponding to the first region of the conductive thin film and the substrate in a part of a region corresponding to the second region of the conductive thin film;

removing the insulating film corresponding to the first region and second region exposed as a result of the formation of the support; and

forming a conducting member electrically connecting the substrate and the conductive thin film in a region corresponding to the second region from which the insulating film has been removed, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

30. (Withdrawn) A stencil mask manufacturing method comprising:

making first openings in a first region of and a second opening in a second region of a conductive thin film of an SOI substrate which includes a substrate, an insulating film formed on

the substrate, and the conductive thin film with the first region and the second region formed on the insulating film;

forming a support by removing the substrate in a region corresponding to the first region;
removing the insulating film exposed as a result of the formation of the support; and
forming a conducting member in the second opening of the conductive thin film, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

31. (Withdrawn) A stencil mask manufacturing method comprising:

forming a concave portion in which an insulating film is exposed in a region corresponding to a second region of a substrate of an SOI substrate which includes the substrate, an insulating film formed on the substrate, and a conductive thin film with a first region and the second region formed on the insulating film;

removing the exposed insulating film;

forming a conducting member in the concave portion, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film;

making openings in a region corresponding to the first region of the conductive thin film;
and

removing the substrate and insulating film corresponding to the first region.

32. (Withdrawn) A mask forming substrate manufacturing method comprising:

forming a concave portion by removing a substrate and an insulating film corresponding to a second region of an SOI substrate which includes the substrate, the insulating film formed

on the substrate, and a conductive thin film formed on the insulating film and having a first region as an opening formation region and the second region around the first region; and

forming a conducting member in the concave portion, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

33. (Withdrawn) A stencil mask manufacturing method comprising:

making a first opening by removing a conductive thin film and an insulating film corresponding to a second region of an SOI substrate which includes a substrate, the insulating film formed on the substrate, and the conductive thin film with a first region and the second region formed on the insulating film;

forming a conducting member in the entire surface of the conductive thin film and in the first opening, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film;

making a second opening by removing the conducting member and the conductive thin film corresponding to the first region; and

forming a support by removing the substrate and insulating film corresponding to the first region.

34. (Withdrawn) A mask forming substrate manufacturing method comprising:

making a first opening by removing a conductive thin film and an insulating film corresponding to a second region of an SOI substrate which includes a substrate, the insulating film formed on the substrate, and the conductive thin film with a first region and the second region formed on the insulating film; and

forming a conducting member in the entire surface of the conductive thin film and in the first opening, the conducting member having a higher electrical conductivity than that of each of the substrate and the conductive thin film.

35. (Currently Amended) A mask forming substrate comprising:

a conductive thin film having a first region and a second region, the second region being outside the first region;

an insulating film formed on the conductive thin film;

a conductive support formed on the insulating film;

an opening formed in the conductive thin film corresponding to a part of the second region and the insulating film; and

a conductive member which is formed in the opening and which connects the conductive thin film and the conductive support electrically.